Hidenori Hiramatsu

List of Publications by Year
in descending order

187 papers	9,399 citations	50566 48 h-index	48101 92 g-index
198 all docs	198 docs citations	198 times ranked	8092 citing authors

#	Article	IF	Citations
1	Electronic and Lattice Thermal Conductivity Switching by 3Dâ”2D Crystal Structure Transition in Nonequilibrium (Pb_{1â”'}_xSn_x)Se. Advanced Electronic Materials, 2022, 8, .	2.6	6
2	Degenerated Hole Doping and Ultraâ€Low Lattice Thermal Conductivity in Polycrystalline SnSe by Nonequilibrium Isovalent Te Substitution. Advanced Science, 2022, 9, e2105958.	5.6	7
3	High-Mobility Metastable Rock-Salt Type (Sn,Ca)Se Thin Film Stabilized by Direct Epitaxial Growth on a YSZ (111) Single-Crystal Substrate. ACS Applied Materials & Interfaces, 2022, 14, 18682-18689.	4.0	1
4	Design, Synthesis, and Optoelectronic Properties of the High-Purity Phase in Layered AETMN₂ (AE = Sr, Ba; TM = Ti, Zr, Hf) Semiconductors. Inorganic Chemistry, 2022, 61, 6650-6659.	1.9	4
5	Characteristic Resistive Switching of Rare-Earth Oxyhydrides by Hydride Ion Insertion and Extraction. ACS Applied Materials & Interfaces, 2022, 14, 19766-19773.	4.0	3
6	Low Residual Carrier Density and High In-Grain Mobility in Polycrystalline Zn₃N₂ Films on a Glass Substrate. ACS Applied Electronic Materials, 2022, 4, 2026-2031.	2.0	0
7	Double Charge Polarity Switching in Sbâ€Doped SnSe with Switchable Substitution Sites. Advanced Functional Materials, 2021, 31, 2008092.	7.8	7
8	Reversible 3D-2D structural phase transition and giant electronic modulation in nonequilibrium alloy semiconductor, lead-tin-selenide. Science Advances, 2021, 7, .	4.7	6
9	Ultrafast optical stress on BaFe2As2. Physical Review Research, 2021, 3, .	1.3	3
10	Large phonon drag thermopower boosted by massive electrons and phonon leaking in LaAlO₃/LaNiO₃/LaAlO₃ heterostructure. Nano Letters, 2021, 21, 9240-9246.	4.5	6
11	Strain Engineering at Heterointerfaces: Application to an Iron Pnictide Superconductor, Cobalt-Doped BaFe₂As₂. ACS Applied Materials & Interfaces, 2020, 12, 50096-50104.	4.0	5
12	Critical temperature and critical current density of hydrogen-doped SmFeAsO epitaxial films fabricated by thermal annealing with binary hydrides. Applied Physics Express, 2020, 13, 073002.	1.1	5
13	Extraordinary Strong Bandâ€Edge Absorption in Distorted Chalcogenide Perovskites. Solar Rrl, 2020, 4, 1900555.	3.1	82
14	Coexistence of magnetism and superconductivity in thin films of the Fe-based superconductor Ba_{1â”'x}La_xFe₂As₂. Journal of Physics Condensed Matter, 2020, 32, 485804.	0.7	6
15	Growth, Properties, and Device Fabrication of Iron-Based Superconductor Thin-Films. , 2020, , 213-241.		0
16	Transition Metalâ€Doped Amorphous Oxide Semiconductor Thinâ€Film Phosphor, Chromiumâ€Doped Amorphous Gallium Oxide. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800198.	0.8	6
17	Heteroepitaxial Thin-Film Growth of a Ternary Nitride Semiconductor CaZn₂N₂. ACS Applied Electronic Materials, 2019, 1, 1433-1438.	2.0	16
18	Performance boosting strategy for perovskite light-emitting diodes. Applied Physics Reviews, 2019, 6, 031402.	5.5	88

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19	Amorphous Oxide Semiconductor Thin-Film Transistors. , 2019, , 573-587.		3
20	Exotic Crystal Structures and Electronic Structures in Novel Structured Inorganic Materials. , 2019, , 107-120.		0
21	Tunable Light Emission through the Range 1.8â€“3.2 eV and p-Type Conductivity at Room Temperature for Nitride Semiconductors, Ca(Mg_{1â€“x}Zn_x)₂N₂ (x =) Tj ETQq1 1 0.784314 rgB	1.9	15
22	New Amorphous Inâ€“Gaâ€“Znâ€“O Thin-Film Transistor-Based Optical Pixel Sensor for Optical Input Signal With Short Wavelength. IEEE Transactions on Electron Devices, 2019, 66, 3841-3846.	1.6	1
23	Insulator-like behavior coexisting with metallic electronic structure in strained FeSe thin films grown by molecular beam epitaxy. Physical Review B, 2019, 99, .	1.1	7
24	Material Design of Green-Light-Emitting Semiconductors: Perovskite-Type Sulfide SrHfS₃. Journal of the American Chemical Society, 2019, 141, 5343-5349.	6.6	59
25	Particulate Generation on Surface of Iron Selenide Films by Air Exposure. Journal of Superconductivity and Novel Magnetism, 2019, 32, 3047-3055.	0.8	3
26	Stabilization and heteroepitaxial growth of metastable tetragonal FeS thin films by pulsed laser deposition. Superconductor Science and Technology, 2019, 32, 054002.	1.8	5
27	Low anisotropic upper critical fields in SmO_{1â^’x}F _x FeAs thin films with a layered hybrid structure. Superconductor Science and Technology, 2019, 32, 044003.	1.8	11
28	Superconducting transition temperatures in the electronic and magnetic phase diagrams of Sr₂VFeAsO_{3â^’Î´}, a superconductor. Journal of Physics Condensed Matter, 2019, 31, 115801.	0.7	7
29	Multiple Color Inorganic Thinâ€Film Phosphor, RE â€Doped Amorphous Gallium Oxide (RE â€‰=â€‰Rare Earth: Pr,) Tj ETQq1 1 0.78 Science, 2019, 216, 1700833.	0.8	15
30	Effects of Base Pressure on Growth and Optoelectronic Properties of Amorphous Inâ€Gaâ€Znâ€O: Ultralow Optimum Oxygen Supply and Bandgap Widening. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700832.	0.8	14
31	Efficient construction method for phase diagrams using uncertainty sampling. Physical Review Materials, 2019, 3, .	0.9	26
32	Superconductivity at 48 K of heavily hydrogen-doped SmFeAsO epitaxial films grown by topotactic chemical reaction using <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Ca</mml:mi><mml:msub><mml:mi mathvariant="normal">H</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review Materials, 2019, 3, .	0.9	19
33	Recent advances in iron-based superconductors toward applications. Materials Today, 2018, 21, 278-302.	8.3	310
34	Pulsed laser deposition of SmFeAsO1â^’ on MgO(100) substrates. Applied Surface Science, 2018, 437, 418-428.	3.1	10
35	Multiple states and roles of hydrogen in p-type SnS semiconductors. Physical Chemistry Chemical Physics, 2018, 20, 20952-20956.	1.3	10
36	Phase transition in CaFeAsH: bridging 1111 and 122 iron-based superconductors. Dalton Transactions, 2018, 47, 12964-12971.	1.6	1

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37	Fabrication, Characterization, and Modulation of Functional Nanolayers. , 2018, , 207-235.		3
38	Multiple Roles of Hydrogen Treatments in Amorphous Inâ€“Gaâ€“Znâ€“O Films. ECS Journal of Solid State Science and Technology, 2017, 6, P365-P372.	0.9	30
39	Highly hydrogen-sensitive thermal desorption spectroscopy system for quantitative analysis of low hydrogen concentration (â^¼1 Ã— 1016 atoms/cm3) in thin-film samples. Review of Scientific Instruments, 2017, 88, 053103.	0.6	13
40	Amorphous Gallium Oxide as an Improved Host for Inorganic Light-Emitting Thin Film Semiconductor Fabricated at Room Temperature on Glass. ECS Journal of Solid State Science and Technology, 2017, 6, P410-P414.	0.9	6
41	Conversion of an ultra-wide bandgap amorphous oxide insulator to a semiconductor. NPG Asia Materials, 2017, 9, e359-e359.	3.8	89
42	Effects of working pressure and annealing on bulk density and nanopore structures in amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors. Japanese Journal of Applied Physics, 2017, 56, 03BB03.	0.8	13
43	BaFe₂(As_{1â^’x}P_x)₂(x= 0.22â^’0.42) thin films grown on practical metalâ€“tape substrates and their critical current densities. Superconductor Science and Technology, 2017, 30, 044003.	1.8	9
44	Key Factors for Insulatorâ€“Superconductor Transition in FeSe Thin Films by Electric Field. IEEE Transactions on Applied Superconductivity, 2017, 27, 1-5.	1.1	11
45	Exploration of Stable Strontium Phosphide-Based Electrides: Theoretical Structure Prediction and Experimental Validation. Journal of the American Chemical Society, 2017, 139, 15668-15680.	6.6	84
46	Structure determination in thin film <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">B</mml:mi><mml:msub><mml:mi mathvariant="normal">a</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:mi mathvariant="normal">L</mml:mi><mml:msub><mml:mi mathvariant="normal">a</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:mi mathvariant="normal">F<	1.1	4
47	Pâ€13: Quantitative Analysis and Deconvolution of Subgap States in Amorphous Inâ€Gaâ€Znâ€O. Digest of Technical Papers SID International Symposium, 2017, 48, 1273-1275.	0.1	1
48	P-187: Electronic Structures of Various Color Light-Emitting Amorphous Oxide Semiconductor Thin Films. Digest of Technical Papers SID International Symposium, 2017, 48, 1974-1976.	0.1	2
49	High-field transport properties of a P-doped BaFe2As2 film on technical substrate. Scientific Reports, 2017, 7, 39951.	1.6	38
50	An Exceptionally Narrow Band-Gap (â^¼4 eV) Silicate Predicted in the Cubic Perovskite Structure: BaSiO₃. Inorganic Chemistry, 2017, 56, 10535-10542.	1.9	16
51	Electron effective mass and mobility limits in degenerate perovskite stannate<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>BaSnO</mml:mi><mml:mn>3</mml:mn></mml:msub> Physical Review B, 2017, 95, .	1.1	45
52	Publisher's Note: Amorphous Gallium Oxide as an Improved Host for Inorganic Light-Emitting Thin Film Semiconductor Fabricated at Room Temperature on Glass [ECS J. Solid State Sci. Technol.,6, P410 (2017)]. ECS Journal of Solid State Science and Technology, 2017, 6, X1-X1.	0.9	0
53	Thin-film Growth and Device Fabrication of Iron-based Superconductors. TEION KOGAKU (Journal of) Tj ETQq1 1 0.784314 rgBT /Over	0.1	1
54	Room-temperature fabrication of light-emitting thin films based on amorphous oxide semiconductor. AIP Advances, 2016, 6, .	0.6	11

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55	Amorphous pnictide semiconductor BaZn2As2 exhibiting high hole mobility. Applied Physics Letters, 2016, 109, .	1.5	2
56	Recent progress in pulsed laser deposition of iron based superconductors. Journal Physics D: Applied Physics, 2016, 49, 345301.	1.3	18
57	Solid phase epitaxial growth of high mobility La:BaSnO3 thin films co-doped with interstitial hydrogen. Applied Physics Letters, 2016, 108, .	1.5	32
58	SnS thin films prepared by H2S-free process and its p-type thin film transistor. AIP Advances, 2016, 6, .	0.6	17
59	Nonequilibrium Rock-Salt-Type Pb-Doped SnSe with High Carrier Mobilities â‰ˆ 300 cm²/(Vs). Chemistry of Materials, 2016, 28, 2278-2286.	3.2	18
60	Why high-pressure sputtering must be avoided to deposit a-In-Ga-Zn-O films. , 2016, , .		1
61	Transparent amorphous oxide semiconductor thin film phosphor, In–Mg–O:Eu. Journal of the Ceramic Society of Japan, 2016, 124, 532-535.	0.5	9
62	Discovery of earth-abundant nitride semiconductors by computational screening and high-pressure synthesis. Nature Communications, 2016, 7, 11962.	5.8	208
63	In-situ growth of superconducting SmO1â^'xFxFeAs thin films by pulsed laser deposition. Scientific Reports, 2016, 6, 35797.	1.6	26
64	Enhanced critical-current in P-doped BaFe2As2 thin films on metal substrates arising from poorly aligned grain boundaries. Scientific Reports, 2016, 6, 36828.	1.6	35
65	Ultrawide band gap amorphous oxide semiconductor, Gaâ€“Znâ€“O. Thin Solid Films, 2016, 614, 84-89.	0.8	13
66	Effects of thermal annealing on elimination of deep defects in amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors. Thin Solid Films, 2016, 614, 73-78.	0.8	13
67	Electric field-induced superconducting transition of insulating FeSe thin film at 35 K. Proceedings of the National Academy of Sciences of the United States of America, 2016, 113, 3986-3990.	3.3	93
68	Novel solid-phase epitaxy for multi-component materials with extremely high vapor pressure elements: An application to KFe2As2. Applied Physics Express, 2016, 9, 055505.	1.1	10
69	Fabrication and opto-electrical properties of amorphous (Zn,B)O thin film by pulsed laser deposition. Journal of the Ceramic Society of Japan, 2015, 123, 523-526.	0.5	2
70	Effects of sulfur substitution in amorphous InGaZnO₄: optical properties and first-principles calculations. Journal of the Ceramic Society of Japan, 2015, 123, 537-541.	0.5	8
71	Effects of residual hydrogen in sputtering atmosphere on structures and properties of amorphous In-Ga-Zn-O thin films. Journal of Applied Physics, 2015, 118, .	1.1	34
72	Heteroepitaxial growth of SnSe films by pulsed laser deposition using Se-rich targets. Journal of Applied Physics, 2015, 118, .	1.1	38

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73	Detection of dead layers and defects in polycrystalline Cu2O thin-film transistors by x-ray reflectivity and photoresponse spectroscopy analyses. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 051211.	0.6	9
74	Exploration of new superconductors and functional materials, and fabrication of superconducting tapes and wires of iron pnictides. Science and Technology of Advanced Materials, 2015, 16, 033503.	2.8	188
75	n-type conversion of SnS by isovalent ion substitution: Geometrical doping as a new doping route. Scientific Reports, 2015, 5, 10428.	1.6	59
76	Vortex Pinning Properties of Phosphorous-Doped <inline-formula> <tex-math notation="TeX">$hbox{BaFe}_{2}hbox{As}_{2}$</tex-math></inline-formula> Epitaxial Films: Comparison Between <inline-formula> <tex-math notation="TeX">$(hbox{La},hbox{Sr})(hbox{Al},hbox{Ta})hbox{O}_{3} $</tex-math></inline-formula> and MgO Substrates. IEEE Transactions on Applied Superconductivity, 2015, 25, 1-5.	1.1	6
77	Charge Compensation by Excess Oxygen in Amorphous Inâ€“Gaâ€“Znâ€“O Films Deposited by Pulsed Laser Deposition. Journal of Display Technology, 2015, 11, 518-522.	1.3	26
78	Origin of Lower Film Density and Larger Defect Density in Amorphous Inâ€“Gaâ€“Znâ€“O Deposited at High Total Pressure. Journal of Display Technology, 2015, 11, 523-527.	1.3	26
79	Electric double-layer transistor using layered iron selenide Mott insulator TlFe1.6Se2. Proceedings of the National Academy of Sciences of the United States of America, 2014, 111, 3979-3983.	3.3	30
80	Effects of High-Temperature Annealing on Operation Characteristics of a-In-Ga-Zn-O TFTs. Journal of Display Technology, 2014, 10, 979-983.	1.3	21
81	High critical-current density with less anisotropy in BaFe2(As,P)2 epitaxial thin films: Effect of intentionally grown c-axis vortex-pinning centers. Applied Physics Letters, 2014, 104, .	1.5	43
82	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. ECS Journal of Solid State Science and Technology, 2014, 3, Q3085-Q3090.	0.9	50
83	Critical factor for epitaxial growth of cobalt-doped BaFe2As2 films by pulsed laser deposition. Applied Physics Letters, 2014, 104, .	1.5	22
84	The atomic structure, band gap, and electrostatic potential at the (112)[11Â¯] twin grain boundary of CuInSe2. Applied Physics Letters, 2014, 104, .	1.5	15
85	SnAs with the NaCl-type Structure: Type-I Superconductivity and Single Valence State of Sn. Chemistry of Materials, 2014, 26, 7209-7213.	3.2	35
86	Film Texture, Hole Transport and Field-Effect Mobility in Polycrystalline SnO Thin Films on Glass. ECS Journal of Solid State Science and Technology, 2014, 3, Q3040-Q3044.	0.9	28
87	Thin film growth of Fe-based superconductors: from fundamental properties to functional devices. A comparative review. Reports on Progress in Physics, 2014, 77, 046502.	8.1	74
88	Growth of high-quality SnS epitaxial films by H2S flow pulsed laser deposition. Applied Physics Letters, 2014, 104, .	1.5	32
89	Narrow Bandgap in Î²-BaZn₂As₂ and Its Chemical Origins. Journal of the American Chemical Society, 2014, 136, 14959-14965.	6.6	33
90	Growth of c-Axis-Oriented Superconducting KFe₂As₂ Thin Films. ACS Applied Materials & Interfaces, 2014, 6, 14293-14301.	4.0	15

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91	Epitaxial growth and electronic structure of a layered zinc pnictide semiconductor, Î²-BaZn2As2. Thin Solid Films, 2014, 559, 100-104.	0.8	13
92	Fabrication and characterization of ZnS:(Cu,Al) thin film phosphors on glass substrates by pulsed laser deposition. Thin Solid Films, 2014, 559, 18-22.	0.8	10
93	Indium-Based Ultraviolet-Transparent Electroconductive Oxyfluoride InOF: Ambient-Pressure Synthesis and Unique Electronic Properties in Comparison with In₂O₃. Journal of the American Chemical Society, 2013, 135, 13080-13088.	6.6	15
94	Unusual pressure effects on the superconductivity of indirectly electron-doped (Ba1â^'xLax)Fe2As2epitaxial films. Physical Review B, 2013, 88, .	1.1	16
95	Superconducting Properties and Phase Diagram of Indirectly Electron-Doped $(hbox{Sr}_{1 -) Tj ETQq1 1 0.784314 rgBT /Overlock 10 T Transactions on Applied Superconductivity, 2013, 23, 7300405-7300405.	1.1	13
96	Ultralow-Dissipative Conductivity by Dirac Fermions in BaFe2As2. Journal of the Physical Society of Japan, 2013, 82, 043709.	0.7	8
97	Magnetic scattering and electron pair breaking by rare-earth-ion substitution in BaFe₂As₂epitaxial films. New Journal of Physics, 2013, 15, 073019.	1.2	18
98	Anomalous scaling behavior in a mixed-state Hall effect of a cobalt-doped BaFe2As2epitaxial film with a high critical current density over 1 MA/cm2. Physical Review B, 2013, 87, .	1.1	16
99	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. Applied Physics Letters, 2013, 103, .	1.5	112
100	Solid-state source of atomic oxygen for low-temperature oxidation processes: Application to pulsed laser deposition of TiO2:N films. Review of Scientific Instruments, 2012, 83, 023903.	0.6	1
101	Identical effects of indirect and direct electron doping of superconducting BaFe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>As<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math> thin films. Physical Review B, 2012, 85, .	1.1	42
102	Structural relaxation in amorphous oxide semiconductor, a-In-Ga-Zn-O. Journal of Applied Physics, 2012, 111, .	1.1	90
103	Thin Film Growth and Device Fabrication of Iron-Based Superconductors. Journal of the Physical Society of Japan, 2012, 81, 011011.	0.7	50
104	Role of lone pair electrons in determining the optoelectronic properties of BiCuOSe. Physical Review B, 2012, 85, .	1.1	42
105	Thin film growth by pulsed laser deposition and properties of 122-type iron-based superconductor AE(Fe_{1â^'x}Co_x)₂As₂(AE=alkaline earth). Superconductor Science and Technology, 2012, 25, 084015.	1.8	42
106	Competition and cooperation of pinning by extrinsic point-like defects and intrinsic strong columnar defects in BaFe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>As<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math> thin films. Physical Review B, 2012, 86, .	1.1	39
107	Microstructure and transport properties of [001]-tilt bicrystal grain boundaries in iron pnictide superconductor, cobalt-doped BaFe2As2. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 515-519.	1.7	35
108	Advantageous grain boundaries in iron pnictide superconductors. Nature Communications, 2011, 2, 409.	5.8	246

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109	Liquid vortex phase and strongc-axis pinning in low anisotropy BaCo_xFe_{2 â^'x}As₂pnictide films. Superconductor Science and Technology, 2011, 24, 055007.	1.8	44
110	Terahertz conductivity measurement of FeSe0.5Te0.5 and Co-doped BaFe2As2 thin films. Physica C: Superconductivity and Its Applications, 2011, 471, 634-638.	0.6	9
111	Characterization of epitaxial Co-doped BaFe2As2 thin films. Physica C: Superconductivity and Its Applications, 2011, 471, 1181-1184.	0.6	5
112	Biaxially textured cobalt-doped BaFe2As2 films with high critical current density over 1â€‚MA/cm2 on MgO-buffered metal-tape flexible substrates. Applied Physics Letters, 2011, 98, 242510.	1.5	110
113	High Critical Current Density 4 MA/cm²in Co-Doped BaFe₂As₂Epitaxial Films Grown on (La,Sr)(Al,Ta)O₃Substrates without Buffer Layers. Applied Physics Express, 2010, 3, 063101.	1.1	83
114	Fabrication and electron transport properties of epitaxial films of electron-doped 12CaOÂ·7Al2O3 and 12SrOÂ·7Al2O3. Journal of Solid State Chemistry, 2010, 183, 385-391.	1.4	19
115	Interface atomic structure of LaCuOSe:Mg epitaxial thin film and MgO substrate. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 229-233.	1.7	3
116	Impurities in FeAs-based superconductor, SrFe2As2, studied by first-principles calculations. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 244-247.	1.7	4
117	Origin of highâ€‰density hole doping and anisotropic hole transport in a wide gap layered semiconductor LaCuOSe studied by firstâ€‰principles calculations. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1636-1641.	0.8	8
118	Josephson junction in cobalt-doped BaFe2As2 epitaxial thin films on (La,Sr)(Al,Ta)O3 bicrystal substrates. Applied Physics Letters, 2010, 96, .	1.5	68
119	Transport and magnetic properties of Co-doped BaFe₂As₂epitaxial thin films grown on MgO substrate. Superconductor Science and Technology, 2010, 23, 105016.	1.8	19
120	DC superconducting quantum interference devices fabricated using bicrystal grain boundary junctions in Co-doped BaFe₂As₂epitaxial films. Superconductor Science and Technology, 2010, 23, 082001.	1.8	47
121	Origins of Hole Doping and Relevant Optoelectronic Properties of Wide Gap p-Type Semiconductor, LaCuOSe. Journal of the American Chemical Society, 2010, 132, 15060-15067.	6.6	43
122	Water-induced superconductivity inSrFe2As2. Physical Review B, 2009, 80, .	1.1	69
123	Pseudoisotropic Upper Critical Field in Cobalt-Doped<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>SrFe</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>As</mml:mi><mml Films. Physical Review Letters, 2009, 102, 117004.	2.9	104
124	Direct imaging of doped fluorine in LaFeAsO1â^'xFx superconductor by atomic scale spectroscopy. Applied Physics Letters, 2009, 95, .	1.5	19
125	Pressure effects onTcof iron-based layered superconductor LaTMPO (TM= Fe, Ni). Journal of Physics: Conference Series, 2009, 150, 052075.	0.3	2
126	Angular and field properties of the critical current and melting line of Co-doped SrFe₂As₂epitaxial films. Superconductor Science and Technology, 2009, 22, 125011.	1.8	23

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127	Tin monoxide as an sâ€orbitalâ€based pâ€type oxide semiconductor: Electronic structures and TFT application. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2187-2191.	0.8	213
128	Atomically-flat, chemically-stable, superconducting epitaxial thin film of iron-based superconductor, cobalt-doped. Solid State Communications, 2009, 149, 2121-2124.	0.9	66
129	Layered mixed-anion compounds: Epitaxial growth, active function exploration, and device application. Journal of the European Ceramic Society, 2009, 29, 245-253.	2.8	21
130	Heteroepitaxial film growth of layered compounds with the ZrCuSiAs-type and ThCr2Si2-type structures: From Cu-based semiconductors to Fe-based superconductors. Physica C: Superconductivity and Its Applications, 2009, 469, 657-666.	0.6	39
131	Low Threshold Voltage and Carrier Injection Properties of Inverted Organic Light-Emitting Diodes with [Ca₂₄Al₂₈O₆₄]⁴⁺(4e^{â^’}) Cathode and Cu_{2â^’x}Se Anode. Journal of Physical Chemistry C, 2009, 113, 18379-18384.	1.5	49
132	Epitaxial film growth and optoelectrical properties of layered semiconductors, LaMnXO (X=P, As, and) Tj ETQq0 0 0 rgBT /Overlock 10 Tf	1.1	33
133	Heteroepitaxial growth of layered semiconductors, LaZnOPn (Pn=P and As). Thin Solid Films, 2008, 516, 5800-5804.	0.8	40
134	Electrical and optical properties of copperâ€based chalcogenide thin films deposited by pulsed laser deposition at room temperature: Toward pâ€channel thin film transistor fabricable at room temperature. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2007-2012.	0.8	7
135	Low and small resistance hole-injection barrier for NPB realized by wide-gap p-type degenerate semiconductor, LaCuOSe:Mg. Organic Electronics, 2008, 9, 890-894.	1.4	29
136	Electronic and magnetic properties of layered LnFePO (Ln=La and Ce). Journal of Physics and Chemistry of Solids, 2008, 69, 2916-2918.	1.9	15
137	Coexistence of superconductivity and antiferromagnetic ordering in the layered superconductor SmFePO. Physical Review B, 2008, 78, .	1.1	31
138	Crystal Structures, Optoelectronic Properties, and Electronic Structures of Layered Oxychalcogenides MCuOCh (M = Bi, La; Ch = S, Se, Te): Effects of Electronic Configurations of M³⁺ Ions. Chemistry of Materials, 2008, 20, 326-334.	3.2	258
139	p -channel thin-film transistor using p-type oxide semiconductor, SnO. Applied Physics Letters, 2008, 93, .	1.5	577
140	Superconductivity in Epitaxial Thin Films of Co-Doped SrFe2As2with Bilayered FeAs Structures and their Magnetic Anisotropy. Applied Physics Express, 2008, 1, 101702.	1.1	103
141	Characterization of copper selenide thin film hole-injection layers deposited at room temperature for use with p-type organic semiconductors. Journal of Applied Physics, 2008, 104, .	1.1	15
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